

NTJD5121N

Power MOSFET

60 V, 295 mA, Dual N-Channel with ESD Protection, SC-88

Features

- Low $R_{DS(on)}$
- Low Gate Threshold
- Low Input Capacitance
- ESD Protected Gate
- This is a Pb-Free Device

Applications

- Low Side Load Switch
- DC-DC Converters (Buck and Boost Circuits)

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	60	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	295	mA
		$T_A = 85^\circ\text{C}$	212	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	304	
		$T_A = 85^\circ\text{C}$	219	
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	250	mW
		$t \leq 5$ s	266	
Pulsed Drain Current	$t_p = 10 \mu\text{s}$	I_{DM}	900	mA
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	210	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	
Gate-Source ESD Rating (HBM)	ESD_{HBM}	2000	V	
Gate-Source ESD Rating (MM)	ESD_{MM}	200	V	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient – Steady State	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5$ s	$R_{\theta JA}$	470	

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

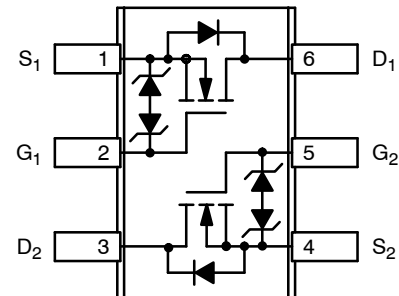


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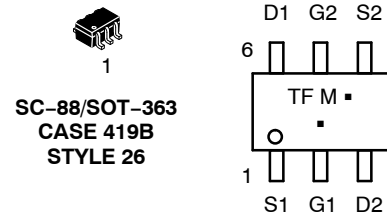
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D Max
60 V	1.6 Ω @ 10 V	295 mA
	2.5 Ω @ 4.5 V	

SC-88 (SOT-363)



Top View

MARKING DIAGRAM & PIN ASSIGNMENT



TF = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTJD5121NT1G	SC-88 (Pb-Free)	3000 / Tape & Reel
NTJD5121NT2G	SC-88 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		92		mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		1.0	μA
			$T_J = 125^\circ\text{C}$		500	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 10	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	1.0	1.7	2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			4.0		mV/ $^\circ\text{C}$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$		1.0	1.6	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$		1.2	2.5	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 200\text{ mA}$		80		S
Gate Resistance	R_G			536		Ω

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 20\text{ V}$		26		pF
Output Capacitance	C_{OSS}			4.4		
Reverse Transfer Capacitance	C_{RSS}			2.5		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 25\text{ V}, I_D = 200\text{ mA}$		0.9		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.2		
Gate-to-Source Charge	Q_{GS}			0.3		
Gate-to-Drain Charge	Q_{GD}			0.28		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 4.5\text{ V}, V_{DD} = 25\text{ V}, I_D = 200\text{ mA}, R_G = 25\ \Omega$		22		ns
Rise Time	t_r			34		
Turn-Off Delay Time	$t_{d(off)}$			34		
Fall Time	t_f			32		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 200\text{ mA}$	$T_J = 25^\circ\text{C}$		0.8	1.2	V
			$T_J = 85^\circ\text{C}$		0.7		

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

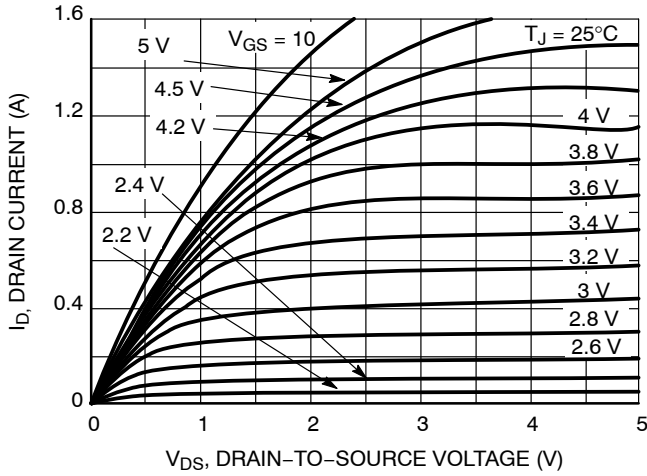


Figure 1. On-Region Characteristics

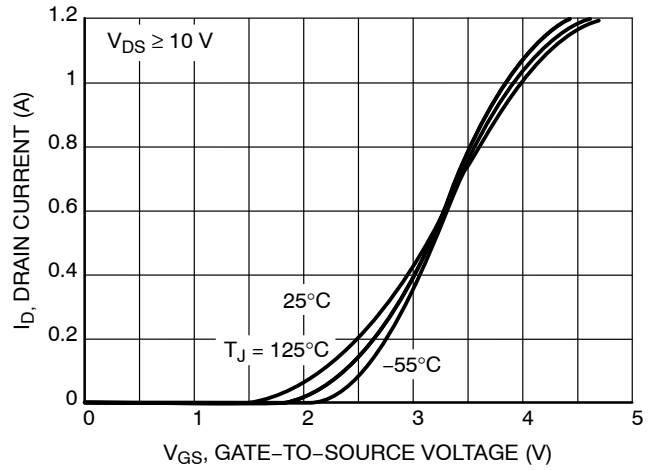


Figure 2. Transfer Characteristics

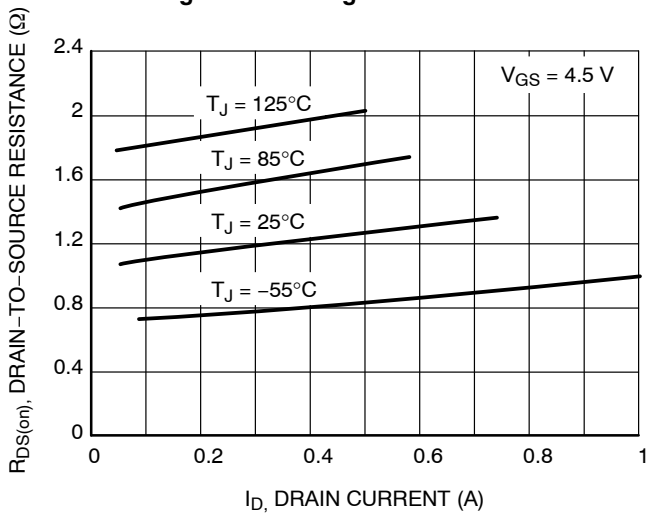


Figure 3. On-Resistance vs. Drain Current and Temperature

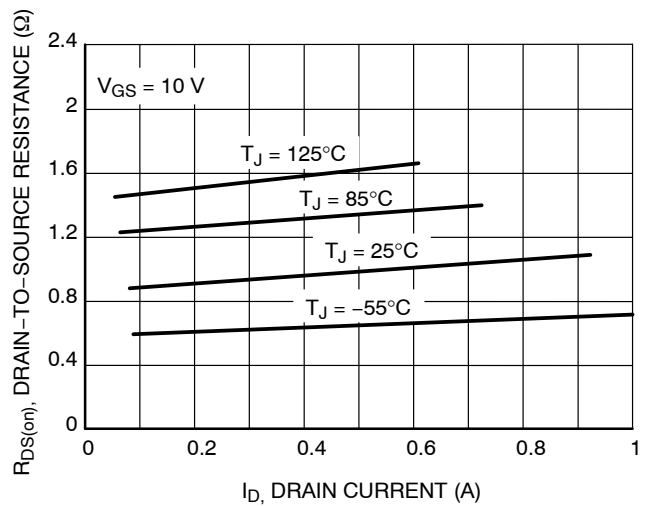


Figure 4. On-Resistance vs. Drain Current and Temperature

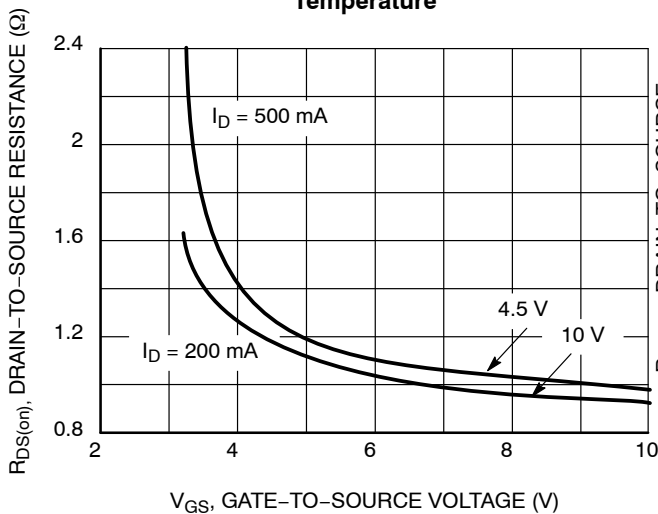


Figure 5. On-Resistance versus Gate-to-Source Voltage

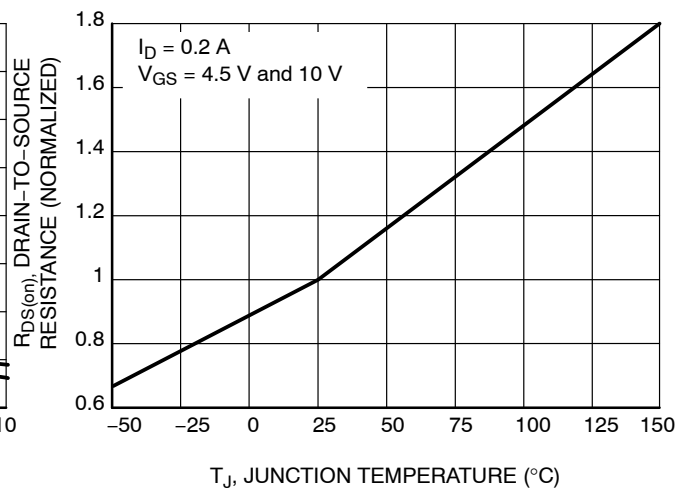


Figure 6. On-Resistance Variation with Temperature

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

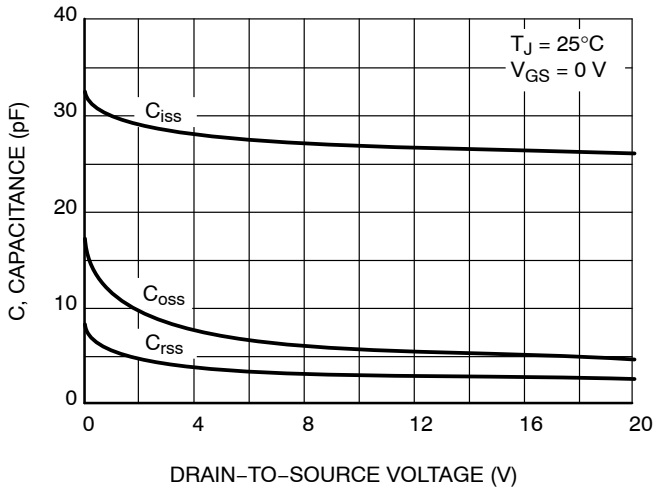


Figure 7. Capacitance Variation

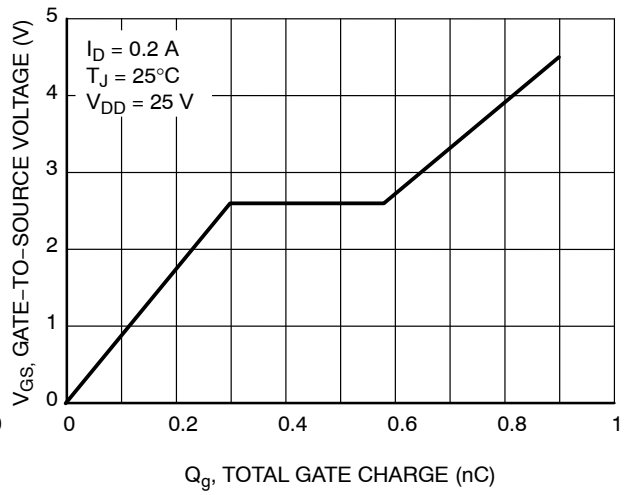


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

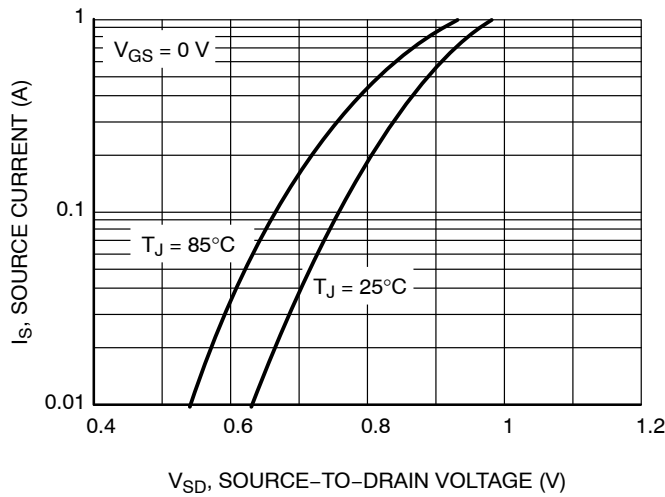


Figure 9. Diode Forward Voltage vs. Current

